

P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I_D (A) ^a	Q_g (Typ.)
- 30	1.9 at $V_{GS} = - 10$ V	- 130	140 nC
	2.7 at $V_{GS} = - 4.5$ V		

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Very low on-resistance $R_{DS(on)}$



RoHS
COMPLIANT

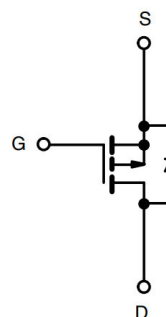
APPLICATIONS

- Load Switch

TO-263 Pin Configuration



Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	- 30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	I_D	- 130	A
	$T_C = 100$ °C		- 83	
Pulsed Drain Current		I_{DM}	- 390	
Avalanche Current		I_{AS}	- 80	
Single Pulse Avalanche Energy ^a		E_{AS}	250	mJ
Power Dissipation	$T_C = 25$ °C ^c	P_D	168	W
	$T_A = 25$ °C ^b		2.5	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +150	°C

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYPICAL	UNIT
Junction-to-Ambient	PCB mount ^b	R_{thJA}	50	°C/W
Junction-to-Case		R_{thJC}	0.75	

Notes

- a. Duty cycle ≤ 1 %.
b. When mounted on 1" square PCB (FR4 material).
c. See SOA curve for voltage derating.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 30			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T	I _D = - 250 μA		- 33		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			5.6		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1		- 3	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 24 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 130			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 20 A		1.9	2.5	mΩ
		V _{GS} = - 4.5 V, I _D = - 20 A		2.7	3.6	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 5 V, I _D = -20 A		98		S
Dynamic ^b						
Input Capacitance	C _{iSS}	V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz		12300		pF
Output Capacitance	C _{oSS}			1310		
Reverse Transfer Capacitance	C _{rSS}			1560		
Total Gate Charge	Q _g	V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 20 A		140		nC
Gate-Source Charge	Q _{gs}			36		
Gate-Drain Charge	Q _{gd}			40		
Gate Resistance	R _g	f = 1 MHz		2.1		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 15 V, I _D = - 20 A, V _{GEN} = - 10 V, R _g = 2.5 Ω		20		ns
Rise Time	t _r			85		
Turn-Off Delay Time	t _{d(off)}			140		
Fall Time	t _f			116		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 130	A
Pulse Diode Forward Current ^a	I _{SM}				- 390	
Body Diode Voltage	V _{SD}	I _S = - 1 A			- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 20 A, di/dt = 100 A/μs, T _J = 25 °C		25		ns
Body Diode Reverse Recovery Charge	Q _{rr}			69		nC
Reverse Recovery Fall Time	t _a			23		ns
Reverse Recovery Rise Time	t _b			16		

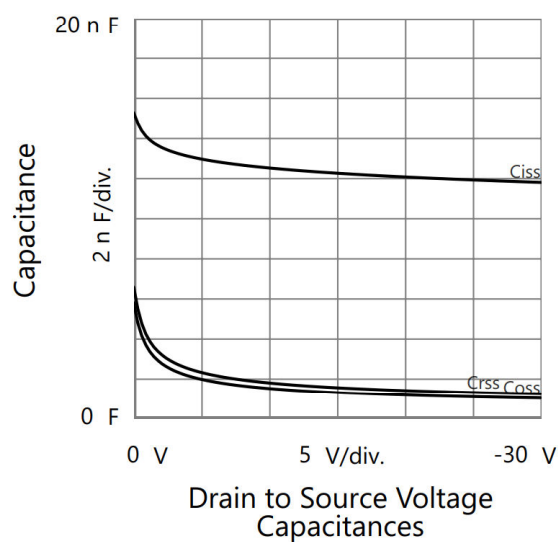
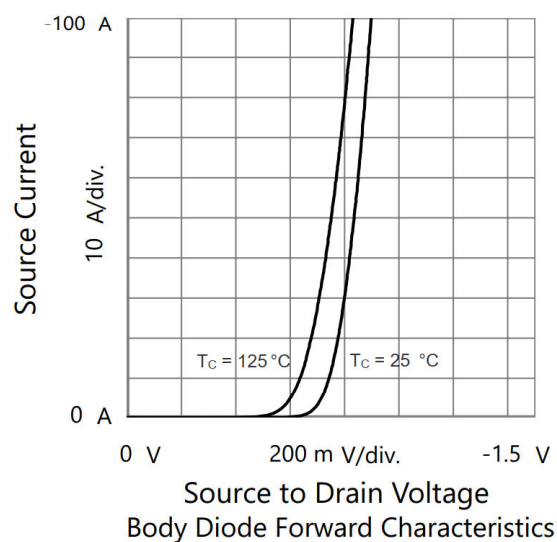
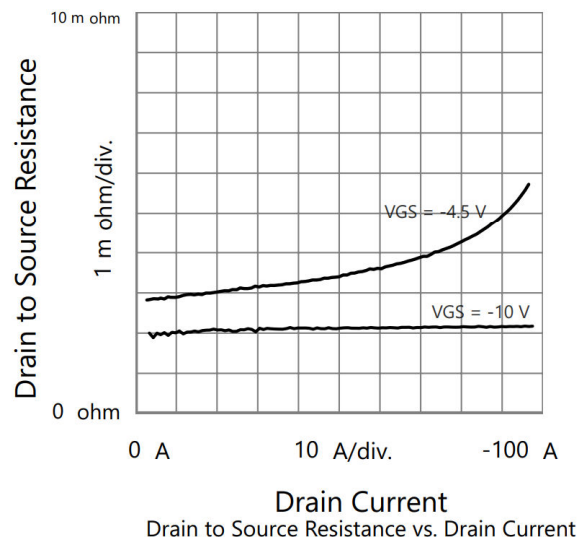
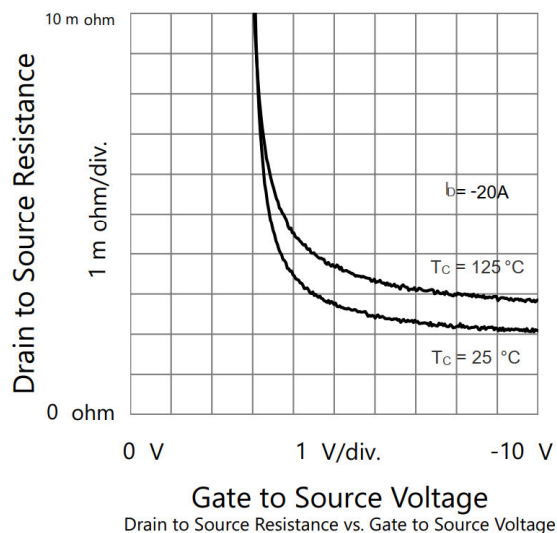
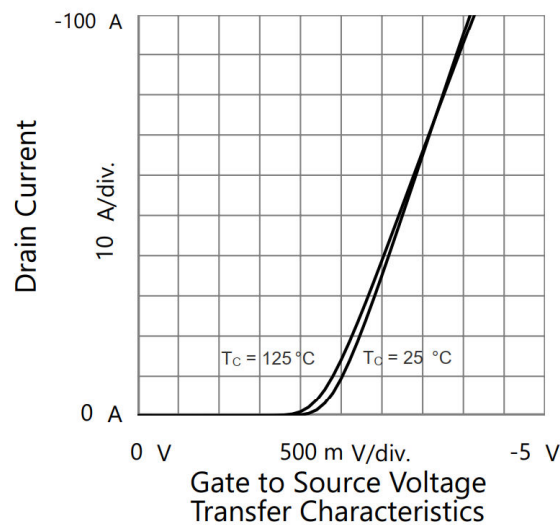
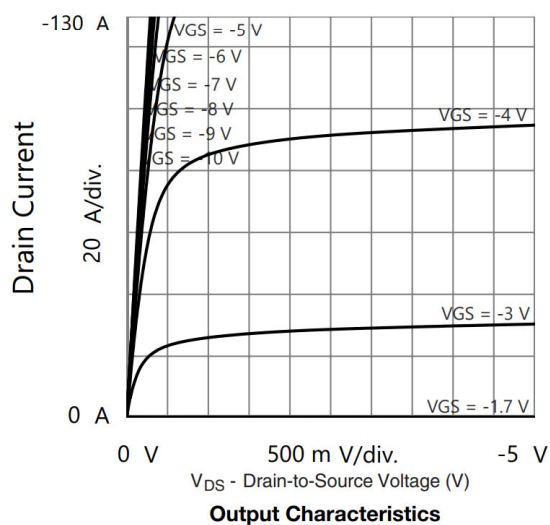
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

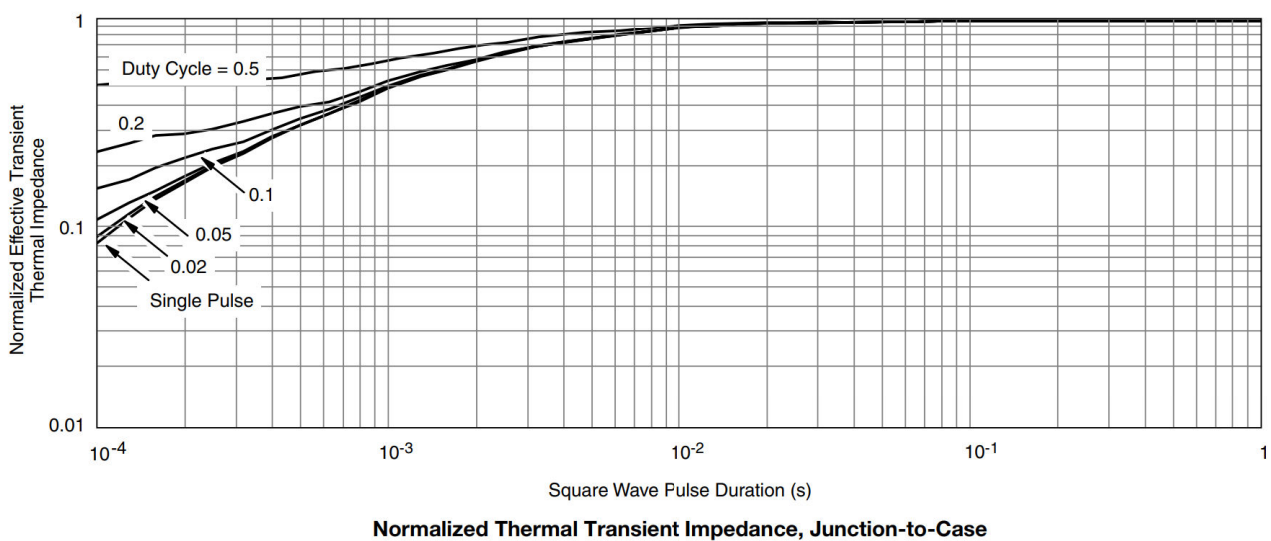
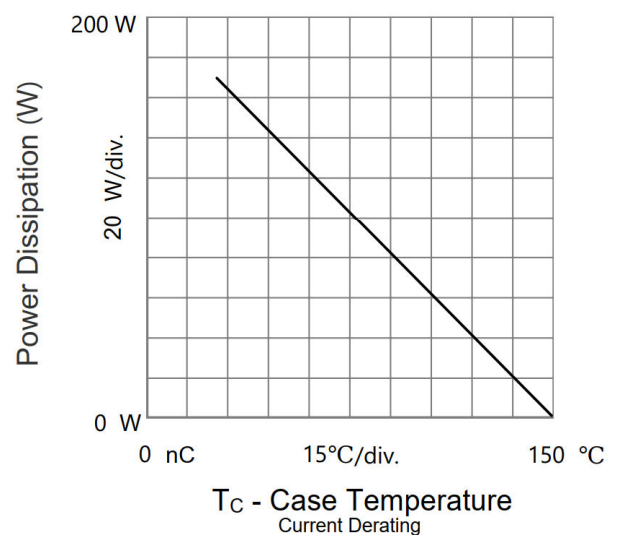
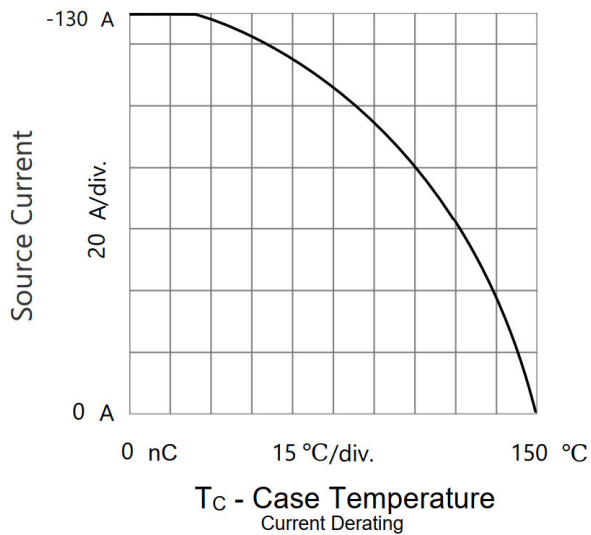
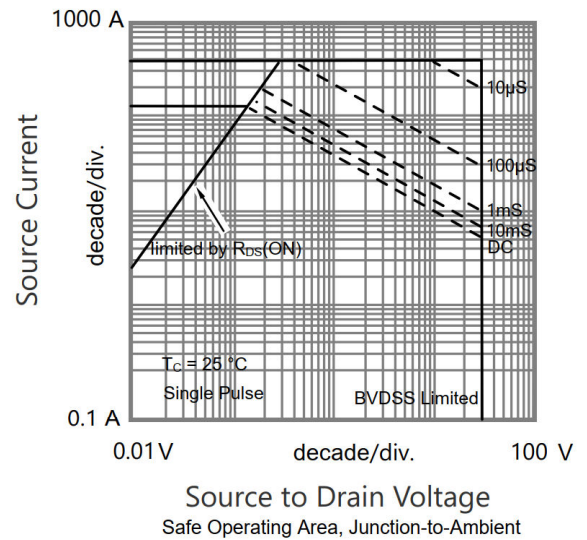
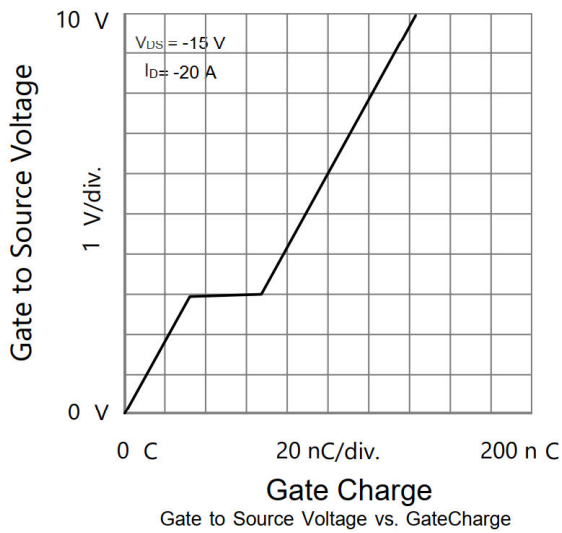
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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